

/ Descriptions

TR-553 SQS Ⅱ 1 Silicon PNP transistor in a TO-220 Plastic Package.

/ Features

Ⅱ - Ⅱ ω" 1 000 3 Ⅱ TIS445T

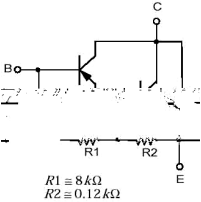
Monolithic construction with built in base-emitter shunt resistors, High DC current gain complement to TIP142T.

/ Applications

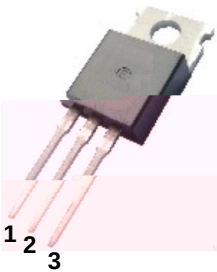
↑ ↑ 000 1 0 Å "Ω

Linear and switching industrial equipment.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

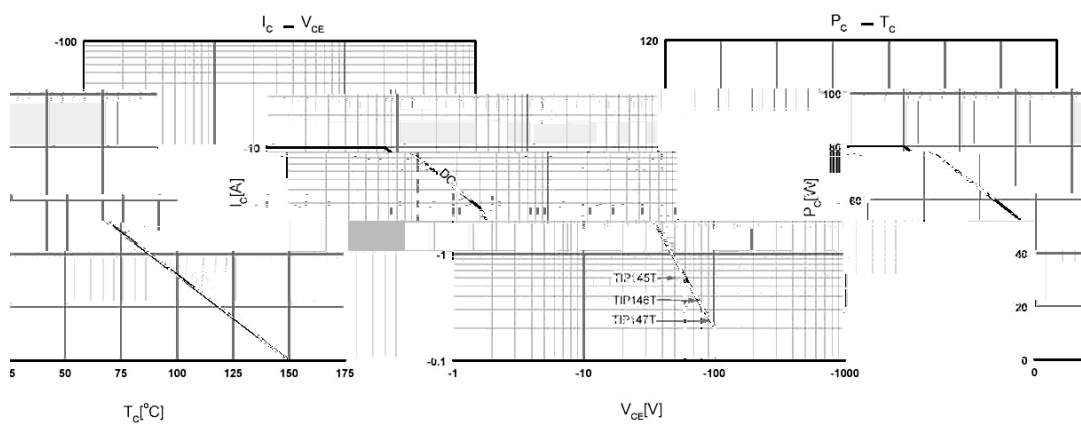
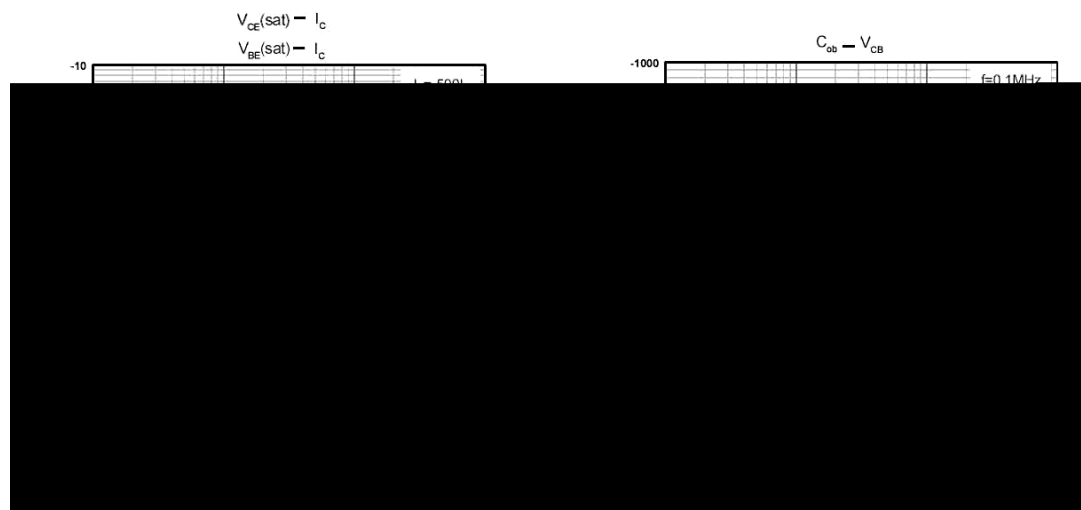
1 " See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

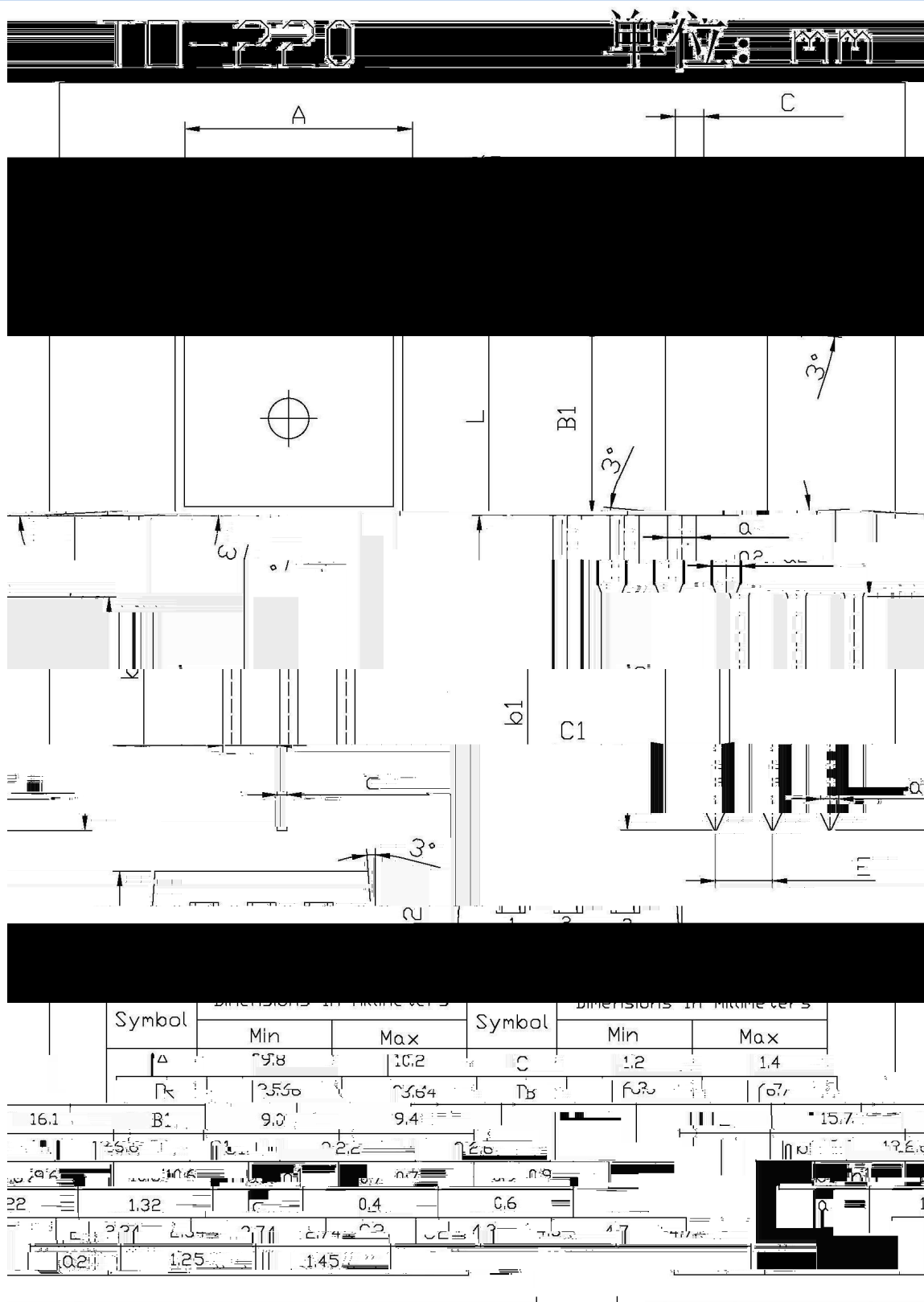
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-10	A
Peak Collector Current	I_{CP}	-15	A
Base Current - Continuous	I_B	-0.5	A
Collector Power Dissipation	$P_C(T_C=25)$	80	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

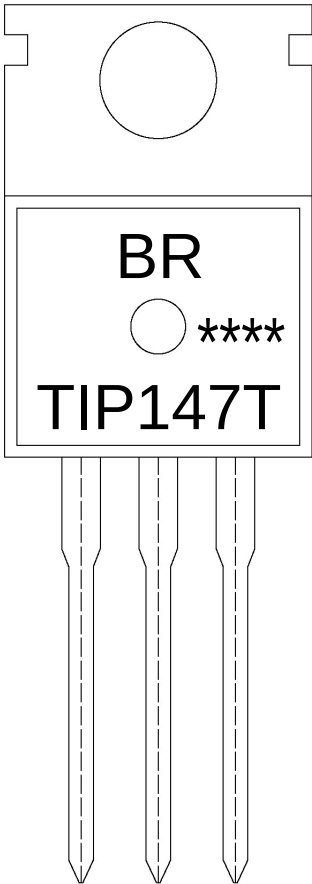
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30mA$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-50V$ $I_B=0$			-2.0	mA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-100V$ $I_E=0$			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-2.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-4.0V$ $I_C=-5.0A$	1000			
	$h_{FE(2)}$	$V_{CE}=-4.0V$ $I_C=-10A$	500			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-5.0A$ $I_B=-10mA$			-2.0	V
	$V_{CE(sat)(2)}$	$I_C=-10A$ $I_B=-40mA$			-3.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-10A$ $I_B=-40mA$			-3.5	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-4.0V$ $I_C=-10A$			-3.0	V
Delay Time	t_D	$V_{CC}=-3V$ $I_C=-5A$ $I_{B1}=-20mA$ $I_{B2}=20mA$ $R_L=6\Omega$		0.15		μs
Rise Time	t_R			0.55		μs
Storage Time	t_{STG}			2.5		μs
Fall Time	t_F			2.5		μs



Package Dimensions

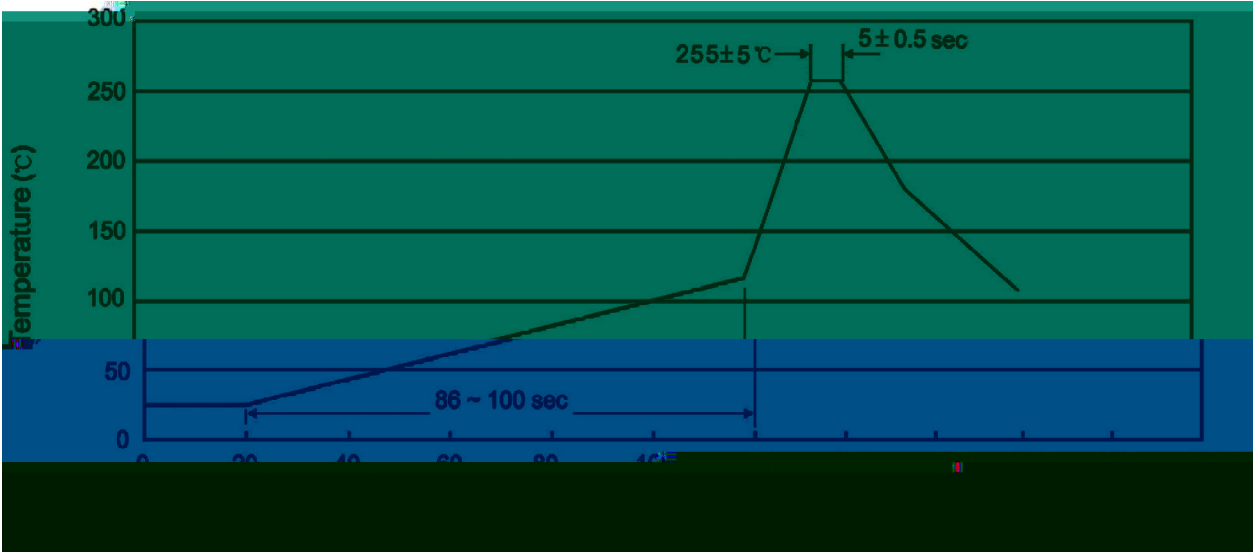


/ Marking Instructions



BR	公司代码
TIP147T	产品型号
****	批次号
Note:	
BR:	Company Code
TIP147T:	Product Type.
****:	Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
1. 预加热: 25~150℃, 时间: 60~90秒;
2. 峰值温度: 255±5℃, 持续时间: 5±0.5秒;
3. 冷却